TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# **TC74HCT652AP**

## **OCTAL BUS TRANSCEIVER/REGISTER (3-STATE)**

The TC74HCT652A is high speed CMOS OCTAL BUS TRANSCEIVER / REGISTER fabricated with silicon gate  $C^2MOS$  technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. Its inputs are compatible with TTL, NMOS, and CMOS output voltage levels.

This device is bus transceiver with 3-state outputs, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the internal registers.

ALL inputs are equipped with protection circuits against static discharge or transient excess voltage.

#### **FEATURES:**

• High Speed------f<sub>MAX</sub> = 60 MHz(typ.)

at  $V_{CC} = 5V$ 

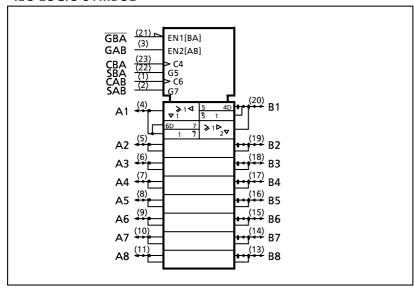
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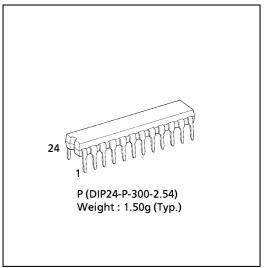
- Low Power Dissipation ············· $I_{CC} = 4\mu A(Max.)$  at Ta = 25°C
- Compatible with TTL Output·····  $V_{IH} = 2.0V(Min.)$

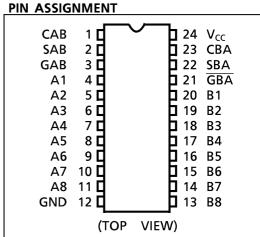
 $V_{IL} = 0.8V \text{ (Max.)}$ 

- Output Drive Capability -------15 LSTTL Loads
- Symmetrical Output Impedance···  $|I_{OH}| = I_{OL} = 6mA(Min.)$
- Balanced Propagation Delays ····· t<sub>pLH</sub> ≃ t<sub>pHL</sub>
- Pin and Function Compatible with 74LS652

### IEC LOGIC SYMBOL







### **APPLICATION NOTES**

- 1) Do not apply a signal to any bus terminal when it is in the out put mode. Damage may result.
- 2) All floating (high impedance) bus terminals must have their input levels fixed by means of pull up or pull down resistors.

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## TRUTH TABLE

GAB	GBA	CAB	СВА	SAB	SBA	Α	В	Function
	Н	X *	X *	х	х	INPUTS Z	INPUTS Z	The output functions of A and B Busses are disabled.
L	П	4		х	x	х	х	Both A and B Busses are used as inputs to the internal flip-flops. Data on the Bus wil be stored on the rising edge of the Clock.
		X *	X *	L	x	INPUTS L H	OUTPUTS L H	The data on the A bus are displayed on the B bus.
Н	Н		X*	L	х	L H	L H	The data on the A Bus are displayed on the B Bus, and are stored into the A storage flip-flops on the rising edge of CAB.
		X *	Х*	Н	х	х	Qn	The data in the A storage flip-flops are displayed on the B Bus.
		<u></u>	X *	Н	×	L H	L H	The data on the A Bus are stored into the A storage flip-flops on the rising edge of CAB, and the stored data propagate directly onto the B Bus.
		X *	X *	x	L	OUTPUTS L H	INPUTS L H	The data on the B bus are displayed on the A bus.
		X *	ſ	х	L	L H	L H	The data on the B Bus are displayed on the A Bus, and are stored into the B storage flip-flops on the rising edge of CBA.
L	L	X *	X*	Х	Н	Qn	x	The data in the B storage flip-flops are displayed on the A Bus.
		X *		x	Н	L H	L H	The data on the B Bus are stored into the E storage flip-flops on the rising edge of CBA and the stored data propagate directly onto the A Bus.
Н	L	X *	X *	н	н	OUTPUTS Qn	OUTPUTS Qn	The data stored to the internal flip-flop are displayed at the A and B burespectively.

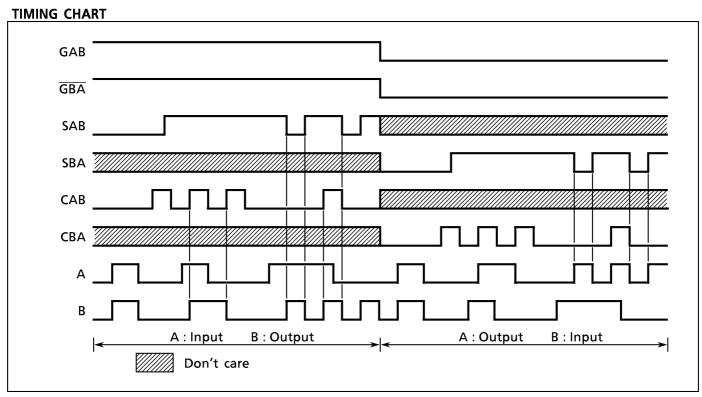
Notes: X: Don't Care

Qn: The data stored into the internal flip-flops by most recent low to high transition of the clock inputs.

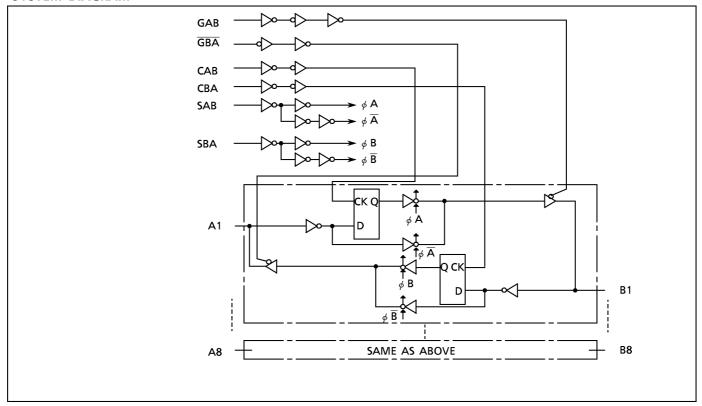
Z: High Impedance

\*: The clock are not internally gated with either GAB or GBA. Therefore, data on the A and/or B Busses may be clocked into the storage flip-flops at any time.

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## **SYSTEM DIAGRAM**



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## **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V <sub>cc</sub>	-0.5~7.0	V
DC Input Voltage	V <sub>IN</sub>	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V <sub>OUT</sub>	$-0.5 \sim V_{CC} + 0.5$	٧
Input Diode Current	I <sub>IK</sub>	± 20	mA
Output Diode Current	I <sub>OK</sub>	± 20	mA
DC Output Current	I <sub>OUT</sub>	±35	mA
DC V <sub>CC</sub> /Ground Current	I <sub>cc</sub>	± 75	mA
Power Dissipation	P <sub>D</sub>	500 (DIP)*	mW
Storage Temperature	$T_{stg}$	<b>−65~150</b>	°C

<sup>\*500</sup>mW in the range of Ta =  $-40^{\circ}$ C~65°C. From Ta = 65°C to 85°C a derating factor of -10mW/°C should be applied up to 300mW.

#### **RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V <sub>cc</sub>	4.5~5.5	V
Input Voltage	V <sub>IN</sub>	0∼V <sub>CC</sub>	V
Output Voltage	V <sub>OUT</sub>	0∼V <sub>cc</sub>	V
Operating Temperature	T <sub>opr</sub>	<b>−40~85</b>	°C
Input Rise and Fall Time	t <sub>r</sub> , t <sub>f</sub>	0~500	ns

#### DC ELECTRICAL CHARACTERISTICS

					7	a = 25°0		Ta = -4		
PARAMETER	SYMBOL	TEST C	V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT	
High - Level Input Voltage	VIH				2.0	_	_	2.0	_	V
Low - Level Input Voltage	=-·-·			4.5 \$ 5.5	_	_	0.8	_	0.8	V
High - Level	V <sub>OH</sub>	V <sub>I N</sub> =	$I_{OH} = -20 \mu A$	4.5	4.4	4.5	_	4.4	_	V
Output Voltage	<b>∨</b> он	V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -6 \text{ mA}$	4.5	4.18	4.31	_	4.13	_	,
Low - Level	V <sub>OL</sub>	V <sub>IN</sub> =	I <sub>OL</sub> = 20 μA	4.5	_	0.0	0.1	_	0.1	V
Output Voltage	VOL	$V_{IH}$ or $V_{IL}$	I <sub>OL</sub> = 6 mA	4.5	_	0.17	0.26	_	0.33	]
3 - State Output Off - State Current	l <sub>oz</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		5.5	_	-	± 0.5	_	± 5.0	μΑ
Input Leakage Current	I <sub>IN</sub>	$V_{IN} = V_{CC}$ or GND		5.5	_	_	± 0.1	-	± 1.0	
Quiescent Supply	I <sub>CC</sub>	$V_{IN} = V_{CC}$ or GND		5.5	_		4.0	_	40.0	$\mu$ A
Current	Ic		Per input:V <sub>IN</sub> = 0.5V or 2.4V Other input:V <sub>CC</sub> or GND		_		2.0	_	2.9	mA

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TIMING REQUIREMENTS (Input  $t_r = t_f = 6ns$ )

PARAMETER	SYMBOL	TEST CONDITION		Ta =	25°C	Ta = −40~85°C	UNIT
FARAIVIETER	STIVIBUL	TEST CONDITION	V <sub>CC</sub> (V)	TYP.	LIMIT	LIMIT	OIVII
Minimum Pulse Width (CK)	t <sub>W(L)</sub> t <sub>W(H)</sub>		4.5 5.5	_	15 14	19 17	
Minimum Set-up Time	t <sub>s</sub>		4.5 5.5	<u> </u>	10 9	13 12	ns
Minimum Hold Time	t <sub>h</sub>		4.5 5.5		5 5	5 5	
Clock Fequency	f		4.5 5.5		31 37	25 30	MHz

AC ELECTRICAL CHARACTERISTICS (Input  $t_r = t_t = 6 \text{ns}$ )

PARAMETER	CVMIDOL	TEST			Ta = 25°C			Ta = - ∠	UNIT	
PARAIVIETER	SYMBOL	CONDITION	CL (pF)	>'S	MIN.	TYP.	MAX.	MIN.	MAX.	וואוטן
Output Transition Time	t <sub>TLH</sub>		50	4.5		7	12	_	15	
- Catput Hansing Hans	t <sub>THL</sub>		100	5.5		6	11	_	14	
Propagation Delay Time	<b>4</b>		50	4.5	_	20	30	–	38	
Tropagation Delay Time	t <sub>pLH</sub>			5.5	_	17	27	_	34	1
(BUS—BUS)	t <sub>pHL</sub>		150	4.5	_	25	38	-	48	
			1.00	5.5		22	34	_	43	_
Propagation Delay Time	<b>+</b>		50	4.5		29	44	_	55	
Tropagation Delay Time	t <sub>pLH</sub>			5.5		26	40	_	50	
(CAB, CBA — BUS)	t <sub>pHL</sub>		150	4.5		34	52	-	65	
	,		.50	5.5		31	47	_	59	_
Propagation Delay Time	_		50	4.5	_	24	34	-	43	
Propagation Delay Time	t <sub>pLH</sub>			5.5	_	21	31	_	39	ns
(SAB, SBA — BUS)	t <sub>pHL</sub>		150	4.5	_	29	42	–	53	
			130	5.5		26	38		48	
Output Enable Time			50	4.5	_	22	33	–	41	
Output Enable Time	t <sub>pZL</sub>	$R_1 = 1k\Omega$		5.5	_	20	30	_	37	
$(GAB, \overline{GBA} - BUS)$	t <sub>pZH</sub>		150	4.5	_	27	41	–	51	
			130	5.5	_	24	37	_	46	
Output Enable Time	t <sub>pLZ</sub>	$R_1 = 1k\Omega$	50	4.5	_	24	35	–	44	
(GAB, GBA – BUS)	t <sub>pHZ</sub>	$K_{\Gamma} = 1K_{7}$	30	5.5	1	22	32	_	40	
Maximum Clock Frequency	fMAX		50	4.5	31	55	_	25	_	MHz
Waximani Clock Trequency	IIVIAX		30	5.5	37	61	_	30	_	101112
Input Capacitance	out Capacitance C <sub>IN</sub> GAB, <del>GBA</del> , SAB, SBA, CA		A, CAB	, CBA	1	5	10	_	10	
Output Capacitance	C <sub>OUT</sub>	An, Bn			_	13	_		_	pF
Power Dissipation Capacitance	C <sub>PD</sub> (1)				_	39	_	_	_	1

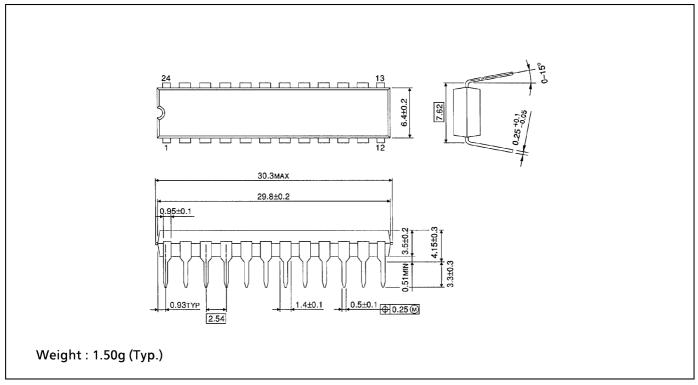
Note(1): CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:  $I_{CC}$  (opr) =  $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 8$  (per bit)

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## DIP 24PIN PACKAGE DIMENSIONS (DIP24-P-300-2.54)

Unit in mm



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